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Defense Electronics Supply Center
Dayton, Ohio

Original date of drawing:
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SIZE
A

CODE IDENT. NO.
14933

REV

MILITARY DRAWING

This drawing is available for use by all Departments and Agencies of the Department of Defense

TITLE: MICROCIRCUITS, DIGITAL ADVANCED CMOS INVERTING OCTAL 3-STATE BUFFER MONOLITHIC SILICON

DWG NO. 5962-87550

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5962-E351-2

DISTRIBUTION STATEMENT A. Approved for public release; distribution is unlimited.

DESC FORM 193
MAY 86

1. SCOPE

1.1 Scope. This drawing describes device requirements for class B microcircuits in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices".

1.2 Part number. The complete part number shall be as shown in the following example:

5962-87550	01	R	X
Drawing number	Device type (1.2.1)	Case outline (1.2.2)	Lead finish per MIL-M-38510

1.2.1 Device types. The device types shall identify the circuit function as follows:

Device type	Generic number	Circuit function
01	54AC240	Octal buffer/line driver with 3-state inverted outputs.
02	54AC11240	Octal buffer/line driver with 3-state inverted outputs.

1.2.2 Case outlines. The case outlines shall be as designated in appendix C of MIL-M-38510, and as follows:

Outline letter	Case outline
J	D-3 (24-lead, 1/2" x 1 1/4"), dual-in-line package
K	F-6 (24-lead, 3/8" x 5/8"), flat package
R	D-8 (20-lead, 1/4" x 1 1/16"), dual-in-line package
S	F-9 (20-lead, 1/4" x 1/2"), flat package
2	C-2 (20-terminal, .350" x .350"), square chip carrier package
3	C-4 (28-terminal, .450" x .450"), square chip carrier package

1.3 Absolute maximum ratings.

Supply voltage range 1/	-0.5 V dc to +6.0 V dc
DC input voltage 1/	-0.5 V dc to V_{CC} +0.5 V dc
DC output voltage 1/	-0.5 V dc to V_{CC} +0.5 V dc
Clamp diode current	±20 mA
DC output current (per pin)	±50 mA
DC V_{CC} or GND current (per pin)	±100 mA
Storage temperature range	-65°C to +150°C
Maximum power dissipation (P_D)	500 mW
Lead temperature (soldering, 10 seconds)	+245°C
Thermal resistance, junction-to-case (θ_{JC}):	
Cases J, K, R, and S	(See MIL-M-38510, appendix C)
Cases 2 and 3	60°C/W 2/
Junction temperature (T_J) 3/	+175°C

1/ Unless otherwise specified, all voltages are referenced to GND.
2/ When a thermal resistance value is included in MIL-M-38510, appendix C, it shall supersede the value stated herein.
3/ Maximum junction temperature shall not be exceeded except for allowable short duration burn-in screening conditions in accordance with method 5004 of MIL-STD-883.

1.4 Recommended operating conditions.

Supply voltage (V_{CC}) 4/	3.0 V dc to 5.5 V dc
Input voltage	0.0 V dc to V_{CC}
Output voltage	0.0 V dc to V_{CC}
Case operating temperature range (T_C)	-55°C to +125°C
Input rise or fall times:	
V_{CC} = 3.6 V	0 to 116 ns (10-90 percent, 40 ns/V)
V_{CC} = 5.5 V	0 to 88 ns (10-90 percent, 20 ns/V)

2. APPLICABLE DOCUMENTS

2.1 Government specification and standard. Unless otherwise specified, the following specification and standard, of the issue listed in that issue of the Department of Defense Index of Specifications and Standards specified in the solicitation, form a part of this drawing to the extent specified herein.

SPECIFICATION

MILITARY

MIL-M-38510 - Microcircuits, General Specification for.

STANDARD

MILITARY

MIL-STD-883 - Test Methods and Procedures for Microelectronics.

(Copies of the specification and standard required by manufacturers in connection with specific acquisition functions should be obtained from the contracting activity or as directed by the contracting activity.)

2.2 Order of precedence. In the event of a conflict between the text of this drawing and the references cited herein, the text of this drawing shall take precedence.

3. REQUIREMENTS

3.1 Item requirements. The individual item requirements shall be in accordance with 1.2.1 of MIL-STD-883, "Provisions for the use of MIL-STD-883 in conjunction with compliant non-JAN devices" and as specified herein.

3.2 Design, construction, and physical dimensions. The design, construction, and physical dimensions shall be as specified in MIL-M-38510 and herein.

3.2.1 Terminal connections. The terminal connections shall be as specified on figure 1.

3.2.2 Truth table. The truth table shall be as specified on figure 2.

3.2.3 Logic diagram. The logic diagram shall be as specified on figure 3.

3.2.4 Case outlines. The case outlines shall be in accordance with 1.2.2 herein.

4/ Operation from 2.0 V dc to 3.0 V dc is provided for compatibility with data retention and battery backup systems. Data retention implies no input transitions and no stored data loss with the following conditions: V_{IH} = 70 percent V_{CC}, $V_{IL} \leq$ 30 percent V_{CC}, $V_{OH} \geq$ 70 percent V_{CC} at -20 µA, $V_{OL} \leq$ 30 percent V_{CC} at 20 µA.

TABLE I. Electrical performance characteristics.

Test	Symbol	Conditions $-55°C \le T_C \le +125°C$		Group A subgroups	Limits Min	Limits Max	Unit
High level output voltage 1/	V_{OH}	$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -50\ \mu A$	$V_{CC} = 3.0$ V	1, 2, 3	2.9		V
			$V_{CC} = 4.5$ V		4.4		
			$V_{CC} = 5.5$ V		5.4		
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -4$ mA	$V_{CC} = 3.0$ V		2.4		
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -24$ mA	$V_{CC} = 4.5$ V		3.7		
			$V_{CC} = 5.5$ V		4.7		
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OH} = -50$ mA	$V_{CC} = 5.5$ V		3.85		
Low level output voltage 1/	V_{OL}	$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 50\ \mu A$	$V_{CC} = 3.0$ V	1, 2, 3		0.1	V
			$V_{CC} = 4.5$ V			0.1	
			$V_{CC} = 5.5$ V			0.1	
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 12$ mA	$V_{CC} = 3.0$ V			0.5	
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 24$ mA	$V_{CC} = 4.5$ V			0.5	
			$V_{CC} = 5.5$ V			0.5	
		$V_{IN} = V_{IH}$ or V_{IL} $I_{OL} = 50$ mA	$V_{CC} = 5.5$ V			1.65	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions $-55°C \le T_C \le +125°C$		Group A subgroups	Limits Min	Limits Max	Unit
High level input voltage 2/	V_{IH}		V_{CC} = 3.0 V		2.1		V
			V_{CC} = 4.5 V		3.15		
			V_{CC} = 5.5 V		3.85		
Low level input voltage 2/	V_{IL}		V_{CC} = 3.0 V			0.9	V
			V_{CC} = 4.5 V			1.35	
			V_{CC} = 5.5 V			1.65	
Input leakage current	I_{IL}	V_M = 0.0 V	V_{CC} = 5.5 V	1, 2, 3		-1.0	µA
	I_{IH}	V_M = 5.5 V				1.0	
Quiescent current	I_{CCH}	$V_{IN} = V_{CC}$ or GND, V_{CC} = 5.5 V		1, 2, 3		160	µA
	I_{CCL}					160	
	I_{CCZ}					160	
Off-state output Leakage current	I_{OZH}	$V_{IN} = V_{CC}$ or GND, V_{CC} = 5.5 V		1, 2, 3		10.0	µA
	I_{OZL}	V_M = 5.5 V or 0.0 V				-10.0	
Input capacitance	C_{IN}	See 4.3.1c		4		8.0	pF
Power dissipation capacitance 3/	C_{PD}	See 4.3.1c		4		55	pF
Functional tests		Tested at V_{CC} = 3.0 V and repeated at V_{CC} = 5.5 V, see 4.3.1d		7, 8			

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions $-55°C \le T_C \le +125°C$		Group A subgroups	Limits Min	Limits Max	Unit
Propagation delay time high-to-low low-to-high A to $\overline{Yn}$ 4/	t_{PHL}	T_C = +25°C C_L = 50 pF R_L = 500Ω See figure 4	V_{CC} = 3.0 V	9	1.0	9.0	ns
			V_{CC} = 4.5 V		1.0	7.0	
	t_{PLH}		V_{CC} = 3.0 V		1.0	9.5	
			V_{CC} = 4.5 V		1.0	10.3	
	t_{PHL}	T_C = -55°C/+125°C C_L = 50 pF R_L = 500Ω See figure 4	V_{CC} = 3.0 V	10, 11	1.0	10.5	ns
			V_{CC} = 4.5 V		1.0	8.0	
	t_{PLH}		V_{CC} = 3.0 V		1.0	11.9	
			V_{CC} = 4.5 V		1.0	8.5	
Output disable time $\overline{OEn}$ to $\overline{Yn}$ 4/	t_{PHZ}	T_C = +25°C C_L = 50 pF R_L = 500Ω See figure 4	V_{CC} = 3.0 V	9	1.0	10.0	ns
			V_{CC} = 4.5 V		1.0	8.5	
	t_{PLZ}		V_{CC} = 3.0 V		1.0	11.0	
			V_{CC} = 4.5 V		1.0	9.0	
	t_{PHZ}	T_C = -55°C/+125°C C_L = 50 pF R_L = 500Ω See figure 4	V_{CC} = 3.0 V	10, 11	1.0	12.5	ns
			V_{CC} = 4.5 V		1.0	10.5	
	t_{PLZ}		V_{CC} = 3.0 V		1.0	13.5	
			V_{CC} = 4.5 V		1.0	11.0	

See footnotes at end of table.

TABLE I. Electrical performance characteristics - Continued.

Test	Symbol	Conditions $-55°C \le T_C \le +125°C$		Group A subgroups	Limits Min	Limits Max	Unit
Output enable time $\overline{OEn}$ to $\overline{Yn}$ 4/	t_{PZH}	T_C = +25°C, C_L = 50 pF, R_L = 500Ω, See figure 4	V_{CC} = 3.0 V	9	1.0	11.5	ns
			V_{CC} = 4.5 V		1.0	7.9	
	t_{PZL}		V_{CC} = 3.0 V		1.0	11.0	
			V_{CC} = 4.5 V		1.0	8.5	
	t_{PZH}	T_C = -55°C/+125°C, C_L = 50 pF, R_L = 500Ω, See figure 4	V_{CC} = 3.0 V	10, 11	1.0	12.5	ns
			V_{CC} = 4.5 V		1.0	9.2	
	t_{PZL}		V_{CC} = 3.0 V		1.0	13.0	
			V_{CC} = 4.5 V		1.0	10.5	

1/ V_{OH} and V_{OL} tests will be tested at V_{CC} = 3.0 V and V_{CC} = 4.5 V. All other voltages are guaranteed, but not tested. Limits shown apply to operation at V_{CC} = 3.3 V ±0.3 V and V_{CC} = 5.0 V ±0.5 V. Transmission driving tests are performed at V_{CC} = 5.5 V with a 2 ms duration maximum.

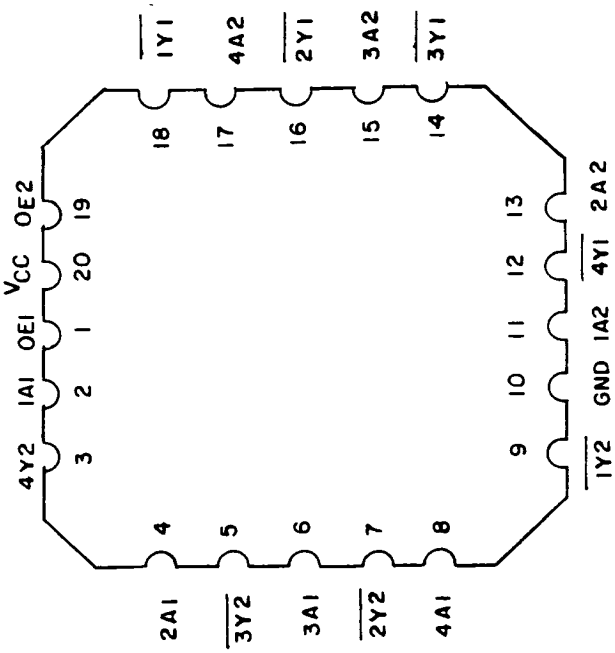
2/ V_{IH} and V_{IL} tests are guaranteed by the V_{OH} and V_{OL} tests.

3/ Power dissipation capacitance (C_{PD}), determines the dynamic power consumption, $PD = (C_{PD} + C_L) V_{CC}^2 f + I_{CC} V_{CC}$, and the dynamic current consumption (IS) is, $IS = (C_{PD} + C_L) V_{CC} f + I_{CC}$.

4/ AC limits at 5.5 V V_{CC} are equal to limits at 4.5 V V_{CC} and guaranteed by testing at 4.5 V V_{CC}. Minimum ac guaranteed for 5.5 V V_{CC} by guardbanding 4.5 V V_{CC} limits to 1.5 ns (minimum).

Device type 01

Case 2



Cases R and S

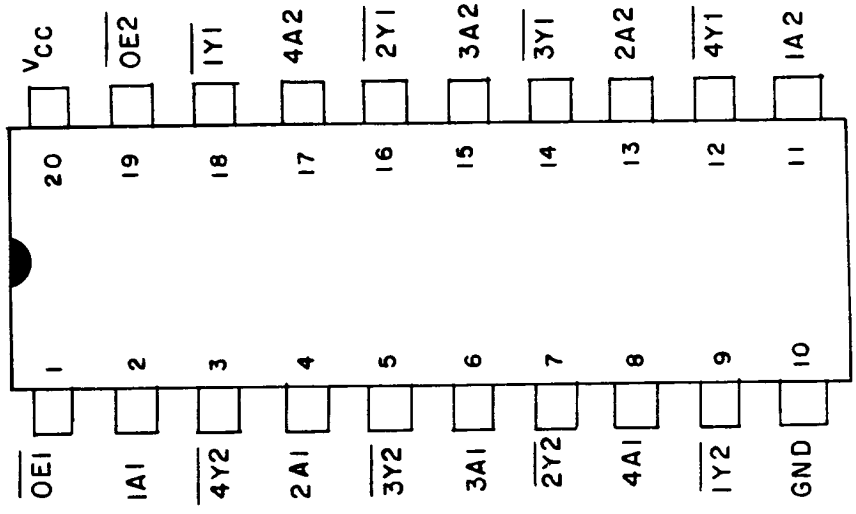


FIGURE 1. Terminal connections.

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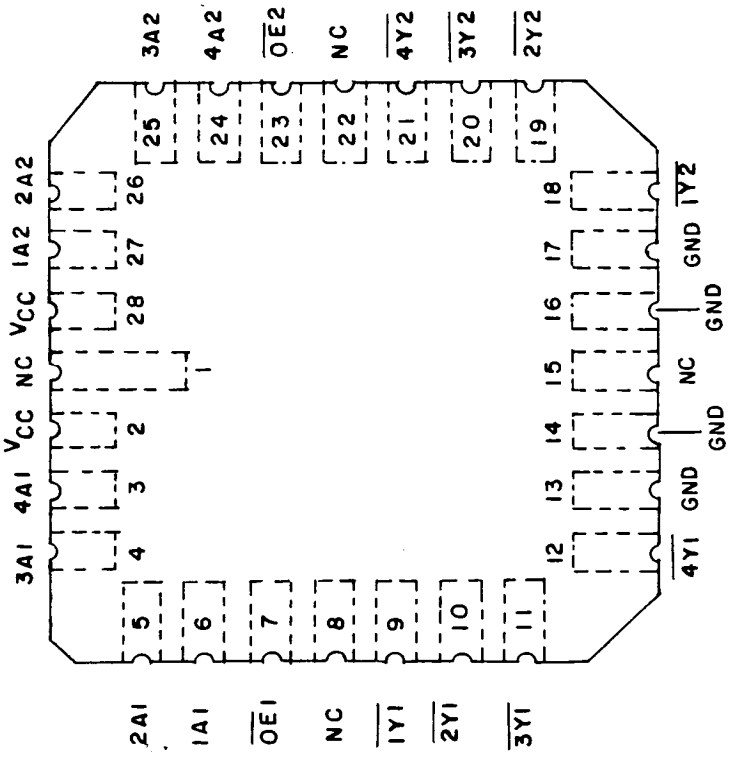
Device type 02

Case 3



Cases J and K

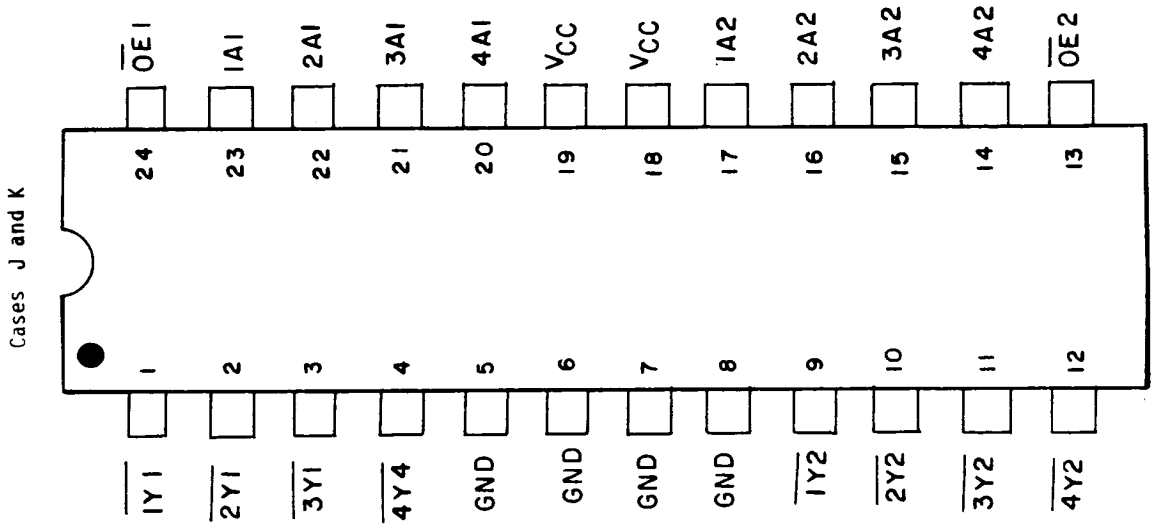


FIGURE 1. Terminal connections - Continued.

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Inputs		Outputs
$\overline{OE1}$, $\overline{OE2}$	A	$\overline{Y}$
L	L	H
L	H	L
H	X	Z

H = High voltage level
L = Low voltage level
X = Immaterial
Z = High impedance

FIGURE 2. Truth table.

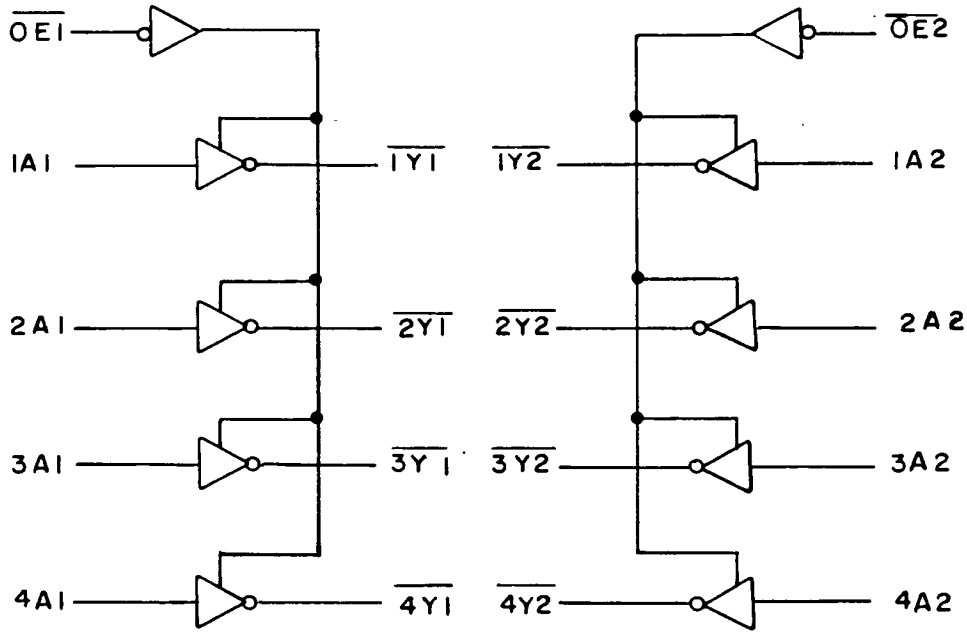
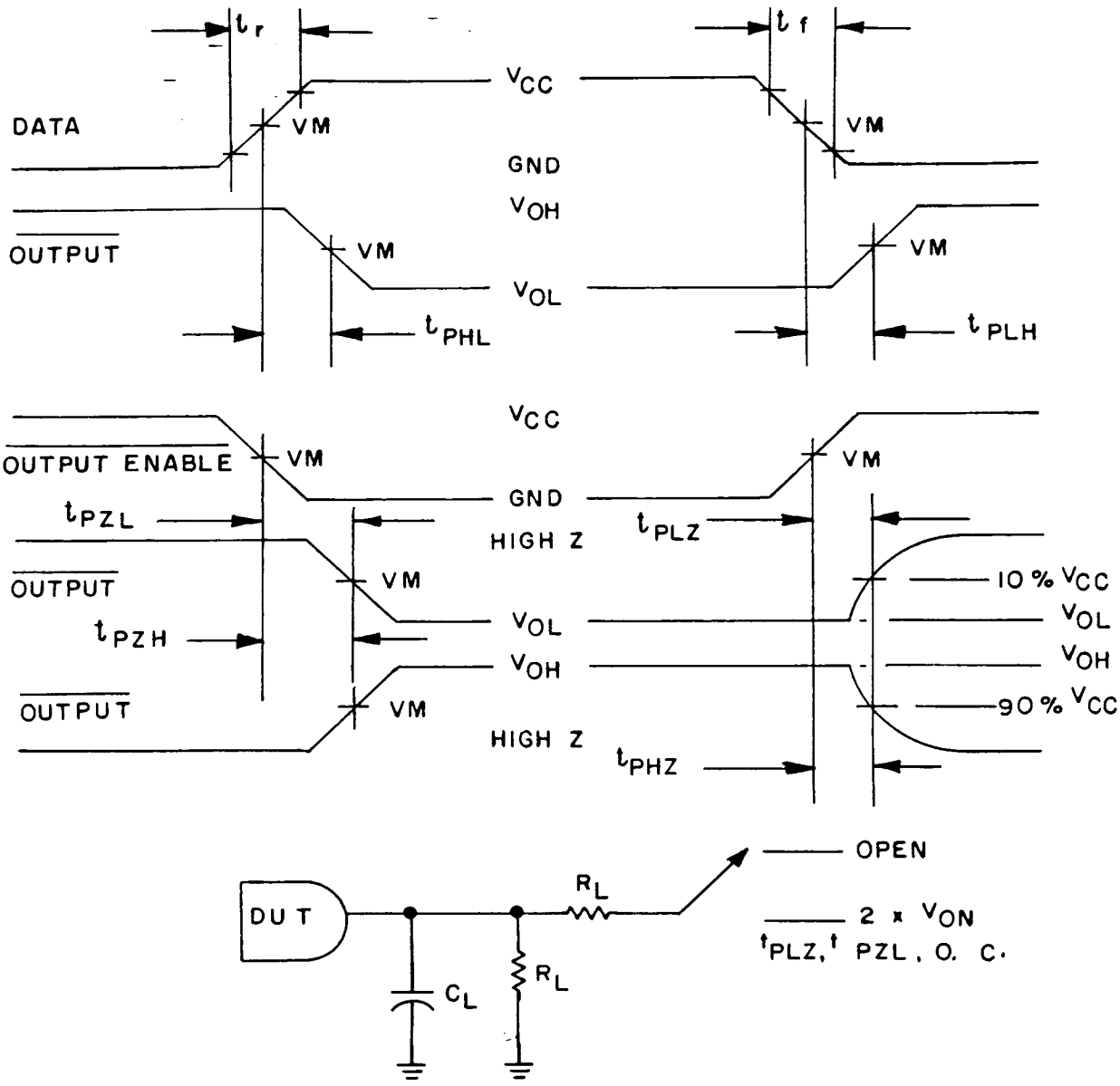


FIGURE 3. Logic diagram.



NOTE:
t_r = t_f = 3.0 ns, 10% to 90% or equivalent
Measure voltage (VM) = 50% of V_{CC}
R_L = 500Ω, C_L = 50 pF or equivalent

FIGURE 4. Switching waveforms.

3.3 Electrical performance characteristics. Unless otherwise specified, the electrical performance characteristics are as specified in table I and apply over the full recommended case operating temperature range.

3.4 Marking. Marking shall be in accordance with MIL-STD-883 (see 3.1 herein). The part shall be marked with the part number listed in 1.2 herein. In addition, the manufacturer's part number may also be marked as listed in 6.4 herein.

3.5 Certificate of compliance. A certificate of compliance shall be required from a manufacturer in order to be listed as an approved source of supply in 6.4. The certificate of compliance submitted to DESC-ECS prior to listing as an approved source of supply shall state that the manufacturer's product meets the requirements of MIL-STD-883 (see 3.1 herein) and the requirements herein.

3.6 Certificate of conformance. A certificate of conformance as required in MIL-STD-883 (see 3.1 herein) shall be provided with each lot of microcircuits delivered to this drawing.

3.7 Notification of change. Notification of change to DESC-ECS shall be required in accordance with MIL-STD-883 (see 3.1 herein).

3.8 Verification and review. DESC, DESC's agent, and the acquiring activity retain the option to review the manufacturer's facility and applicable required documentation. Offshore documentation shall be made available onshore at the option of the reviewer.

4. QUALITY ASSURANCE PROVISIONS

4.1 Sampling and inspection. Sampling and inspection procedures shall be in accordance with section 4 of MIL-M-38510 to the extent specified in MIL-STD-883 (see 3.1 herein).

4.2 Screening. Screening shall be in accordance with method 5004 of MIL-STD-883, and shall be conducted on all devices prior to quality conformance inspection. The following additional criteria shall apply:

a. Burn-in test (method 1015 of MIL-STD-883).

(1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.5 herein).

(2) T_A = +125°C, minimum.

b. Interim and final electrical test parameters shall be as specified in table II herein, except interim electrical parameter tests prior to burn-in are optional at the discretion of the manufacturer.

4.3 Quality conformance inspection. Quality conformance inspection shall be in accordance with method 5005 of MIL-STD-883 including groups A, B, C, and D inspections. The following additional criteria shall apply.

4.3.1 Group A inspection.

a. Tests shall be as specified in table II herein.

b. Subgroups 5 and 6 in table I, method 5005 of MIL-STD-883 shall be omitted.

c. Subgroup 4 (C_{IN} and C_{PD} measurement) shall be measured only for the initial test and after process or design changes which may affect input capacitance.

d. Subgroups 7 and 8 tests sufficient to verify the truth table.

4.3.2 Groups C and D inspections.

a. End-point electrical parameters shall be as specified in table II herein.

b. Steady-state life test (method 1005 of MIL-STD-883) conditions:

(1) Test condition A, B, C, or D using the circuit submitted with the certificate of compliance (see 3.5 herein).

(2) T_A = +125°C, minimum.

(3) Test duration: 1,000 hours, except as permitted by appendix B of MIL-M-38510 and method 1005 of MIL-STD-883.

TABLE II. Electrical test requirements.

MIL-STD-883 test requirements	Subgroups (per method 5005, table I)
Interim electrical parameters (method 5004)	---
Final electrical test parameters (method 5004)	1*,2,3,7,8,9
Group A test requirements (method 5005)	1,2,3,7,8,9, 10,11
Groups C and D end-point electrical parameters (method 5005)	1, 2, 3
Additional electrical subgroups for group C periodic inspections	---

*PDA applies to subgroup 1.

5. PACKAGING

5.1 Packaging requirements. The requirements for packaging shall be in accordance with MIL-M-38510.

6. NOTES

6.1 Intended use. Microcircuits conforming to this drawing are intended for use when military specifications do not exist and qualified military devices that will perform the required function are not available for OEM application. When a military specification exists and the product covered by this drawing has been qualified for listing on QPL-38510, the device specified herein will be inactivated and will not be used for new design. The QPL-38510 product shall be the preferred item for all applications.

6.2 Replaceability. Replaceability is determined as follows:

a. Microcircuits covered by this drawing will replace the same generic device covered by a contractor-prepared specification or drawing.

b. When a QPL source is established, the part numbered device specified in this drawing will be replaced by the microcircuit identified as part number M38510/75703B--.

Comments on this drawing should be directed to DESC-ECS, Dayton, Ohio 45444, or telephone 513-296-5375.

6.4 Approved sources of supply. Approved sources of supply are listed herein. Additional sources will be added as they become available. The vendors listed herein have agreed to this drawing and a certificate of compliance (see 3.5 herein) has been submitted to DESC-ECS.

Military drawing part number	Vendor CAGE number	Vendor similar part number 1/	Replacement military specification part number
5962-8755001RX	07263	54AC240 DMQB	M38510/75703BRX
5962-8755001SX	07263	54AC240 FMQB	
5962-87550012X	07263	54AC240 LMQB	M38510/75703B2X
5962-8755002JX	01295	SNJ54AC11240J	M38510/75723BJX
5962-8755002KX	01295	SNJ54AC11240W	
5962-87550023X	01295	SNJ54AC11240FK	M38510/75723B3X

1/ Caution. Do not use this number for item acquisition. Items acquired to this number may not satisfy the performance requirements of this drawing.

Vendor CAGE number	Vendor name and address
07263	Fairchild Semiconductor 333 Western Avenue South Portland, ME 04106
01295	Texas Instruments, Inc. P.O. Box 6448 Midland, TX 79701